

## IR-44

1. Color                                    Infrared
2. Materials                              GaAs/GaAs
3. Electrode                              P(anode) side : Al  
                                                    N(cathode) side : Au
4. Electrode pattern                    Fig.1,2
5. Chip size                                0.185mm X 0.185mm X 0.180mmH (Fig.1)
6. Emission area                        0.160mm X .160mm (Fig.1)
7. Electro-Optical characteristics

Parameters	Symbol	Condition	Min	Typ	Max	Unit
Power	Po	IF=20mA	0.4	0.75	—	mW
Forward Voltage	VF	IF=20mA	—	1.3	1.5	V
Reverse Current	IR	VR=5V	—	—	10	uA
Peak Wavelength	* λp	IF=20mA	—	940	—	nm
Spectral Radiation Bandwidth	* Δλ	IF=20mA	—	40	—	nm

\* 「\*」 mark is reference data

\* Power measurement at Resonac Photonics.

8. Recommended bonding method    Ultra-sonic method or a combination of ultra-sonic and thermo-compression methods.

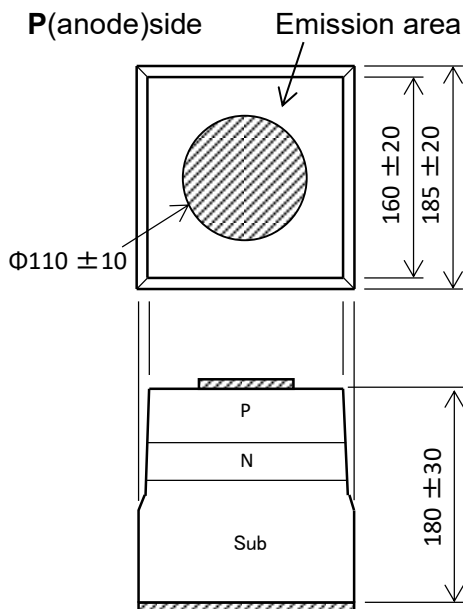


Fig.1 : Chip size and Emission area

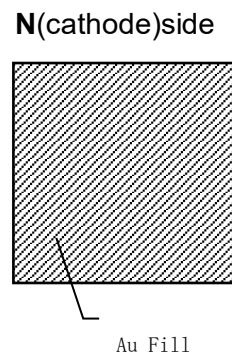


Fig.2 : Electrode pattern

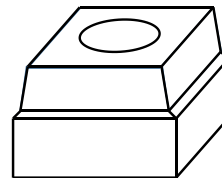


Fig.3 : No roughing

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